

Amendment Dated: July 24, 2003

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS

Claims 1-17. (Canceled)

18. (Original) A method of manufacturing a semiconductor device, comprising the steps of: forming an insulating film on a semiconductor substrate;
forming a conductive film on the insulating film;
forming a nitrogen-containing oxide film over the semiconductor substrate, insulating film, and conductive film;
forming a boron-doped phosphorus silicate glass (BPSG) film after the nitrogen-containing oxide film; and
carrying out a heat treatment on the BPSG film in an oxidizing atmosphere.

19. (Original) The method of claim 18, wherein the step of forming a nitrogen-containing oxide film includes the step of carrying out a heat treatment in a dinitrogen monoxide (N₂O) gas.

20. (Original) The method of claim 18, wherein the step of forming a nitrogen-containing oxide film includes the steps of:
forming a thermal oxide film on exposed surfaces of the semiconductor substrate and conductive film; and

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heat-treating the thermal oxide film in a dinitrogen monoxide (N_2O) gas or a nitric monoxide (NO) gas.

21. (Original) The method of claim 18, wherein the step of forming a nitrogen-containing oxide film includes the steps of:

forming a silicon oxide film on exposed surfaces of the semiconductor substrate, insulating film, and conductive film; and

heat-treating the silicon oxide film in a dinitrogen monoxide (N_2O) gas or a nitric monoxide (NO) gas.

22. (Original) The method of claim 18, wherein the oxidizing atmosphere contains water vapor.